

Fig 1: Ferroelectric capacitor element

Form: capacitorferroelectric:<instance name> n1 n2 <parameter list>
n1, n2 are the element terminals

Parameters:

Parameter	Type	Default Value	Required?
epsid: Interfacial capacitance density (F/m ²)	DOUBLE	32e-3	no
epsb0: Bulk capacitance zero-bias permittivity (F/m)	DOUBLE	170	no
a: Area of cross-section of the parallel plate capacitor (m ²)	DOUBLE	n/a	yes
d: Total capacitor thickness (m)	DOUBLE	n/a	yes
t: 2 * (Interfacial Capacitor thickness at the plate dielectric interface) (m)	DOUBLE	5e-9	no
k: Fringing capacitance constant (F)	DOUBLE	1.6e-15	no
alpha3: Describes the non-linearity of the material in the Landau-Devonshire-Ginzburg model (m ² /C ² F)	DOUBLE	3.3e-3	no
T0: Curie-Weiss temperature for a particular BST film thickness (deg C)	DOUBLE	-167	no
T: Current Temperature of the sample (deg C)	DOUBLE	-73	no
beta: Temperature Coefficient of Capacitance (TCC) at zero bias (ppm/deg C)	DOUBLE	600	no
p: Device periphery for fringing capacitance calculations (m)	DOUBLE	n/a	yes

Example:

```
.model c_ferro capacitorferroelectric ( epsid =50e-3 epsb0=170 a=2000e-12 t=5e-9  
+ k=2.0e-15 alpha3=3.3e-3 T0=-167 T=-80 beta=1000 p=240e-9)  
capacitorferroelectric: cf1 3 0 model="c_ferro" d=125e-9
```

Details:

This element models a non-linear ferroelectric capacitor. A parallel plate physical model of the capacitor is considered although this concept can be further extended to model ferroelectric IDCs (inter-digitated capacitors) and gap capacitors. This model accounts for interfacial, bulk capacitance and fringing capacitance. It also considers thickness and temperature dependence of the high-permittivity ferroelectric material. This model can be used during time-domain analysis. Leakage and breakdown currents are not modeled.

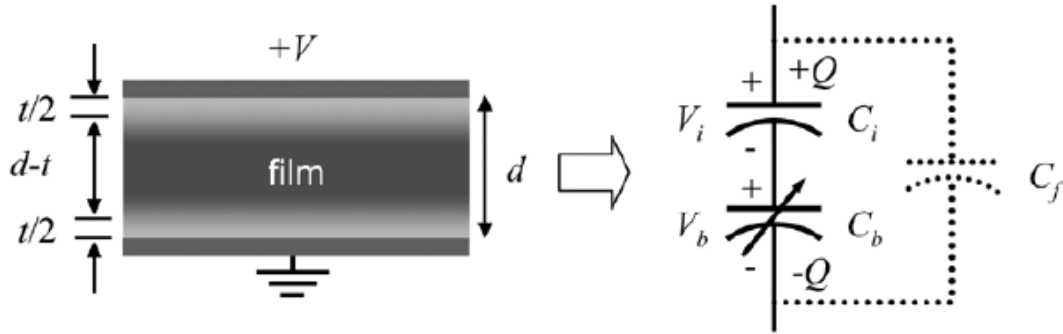


Fig 2: Ferroelectric capacitor model that includes the effect of the interfacial capacitance, bulk capacitance and fringing capacitance[2].

Data collected from experiments indicates that a “dead” layer non-tunable capacitance exists in series with a bulk non-linear capacitance. The voltage applied is dropped across a series combination of the interface capacitance at the two plate dielectric interfaces and the bulk ferroelectric dielectric material. While this model characterizes large area capacitors ($\approx 2000\mu\text{m}^2$) very well, small area capacitors need an additional fringing capacitance in parallel as shown in Fig. 2 to account for their reduced tunability compared to large area capacitors[2]. This model ignores the space-charge buildup near the electrodes.

With reference to Fig 2, both the interfacial capacitances are collectively described by a linear charge-voltage equation:

$$V_i = \frac{Q}{C_i}; C_i = \frac{\epsilon_i A}{t} \quad (1.1)$$

Here the interfacial capacitance density $\frac{\epsilon_i}{t}$ is determined experimentally from a series of devices of varying thickness.

The bulk is described by a nonlinear equation from the Landau-Devonshire-Ginzburg (LDG) model [1] by:

$$V_b = \frac{Q}{C_{b,max}} + KQ^3 \quad (1.2)$$

$$\frac{1}{C_{b,max}} = \alpha_1 \frac{(d-t)}{A} \text{ and } K = \alpha_3 \frac{(d-t)}{A} \quad (1.3)$$

The total voltage across the device is then:

$$V_{cap} = Q \left(\frac{1}{C_i} + \frac{1}{C_{b,max}} \right) + KQ^3 \quad (1.4)$$

The fringing capacitance is independent of the field and thickness and is given by

$$C_f = k \frac{P}{d} \quad (1.5)$$

$$\epsilon_b(T) \approx \epsilon_{b0} [1 - \beta(T - T_0)] \quad (1.6)$$

In the equations above

ϵ_i = Interfacial material dielectric permittivity (F/m²)

ϵ_{b0} = Bulk dielectric material zero-bias permittivity (F/m)

A = Area of cross-section of the parallel plate capacitor (m²)

d = Total capacitor thickness (m)

t = Interfacial capacitance thickness (m)

k = Fringing capacitance constant (F)

α_3 = Describes the non-linearity of the material in the Landau-Devonshire-Ginzburg model (m²/C²F)

$\epsilon_b(T)$ = Temperature dependent bulk dielectric zero-bias permittivity (F/m)

β = Temperature Coefficient of capacitance (TCC) at zero bias (ppm/deg C)

T = Current Temperature of the sample (deg C)

T_0 = Curie-Weiss temperature for a particular BST film thickness (deg C)

Q = Charge on the capacitor (C)

Netlist file circuit:

The netlist model used to prove the correctness of the model is a RC coupling circuit. The netlist is run with three different values of output resistance 'R' to change the RC time-constant of the circuit as shown in the fig 3. The input square wave changes shape based on the RC time constant in comparison with the 'T' – the time period of the square wave.

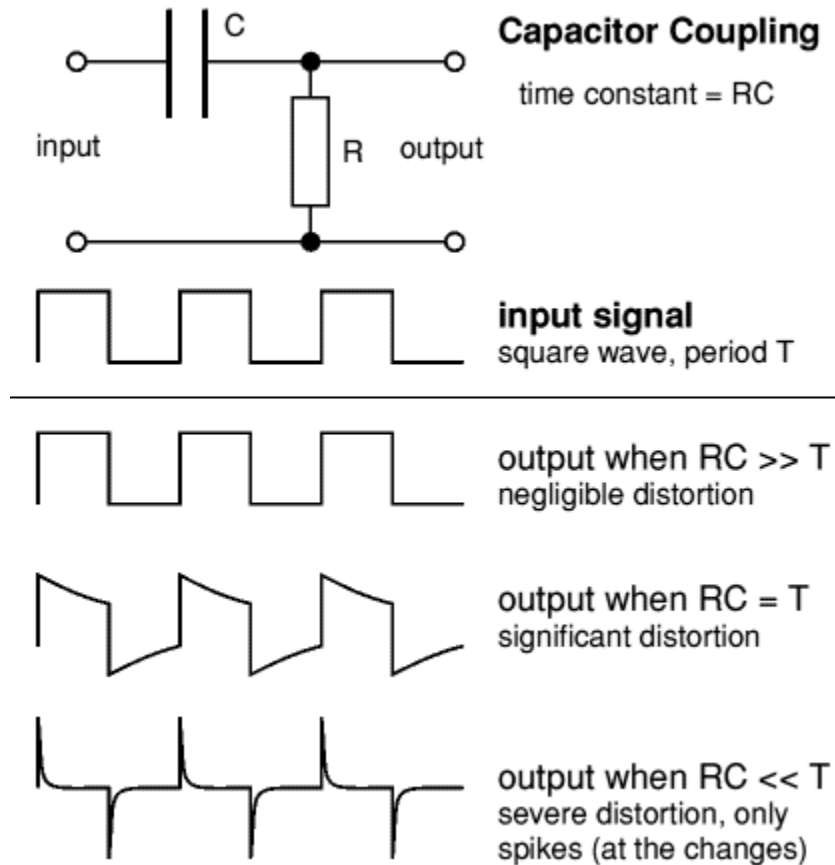


Fig3. Input square wave and output signal wave shapes based on the RC time constant value in comparison with 'T' – the time period of the wave [6].

Example of Transient analysis (.TRAN2) Fixed time steps, time-stepping nonlinear analysis

Netlist File:

*** Transient Analysis for the Ferroelectric capacitor

.options verbose

```

*.svtr tstop = 2e-5 n_freqs = 70 tstep = 0.25e-6
*.svtr tstop = 1e-4 n_freqs = 70 tstep = 0.25e-6

.tran2 tstop = 1e-4 tstep = 0.50e-6 out_steps=1 im=2

*vsource:1 1 0 vac=1.0 f=0.3e5 phase=90

vpulse:v1 1 0 v1=0 v2=5 td=0 tr=0.05e-5 tf=0.05e-5 pw=1.5e-5 per=3.5e-5
capacitorferroelectric:cf1 1 2 a=6500e-12 d=150e-9 p=160e-9

*RC time constant << T
*resistor:rin1 2 0 r=1000

*RC time constant ~ T
*resistor:rin1 2 0 r=25000

*RC time constant >> T
resistor:rin1 2 0 r=1000000

.options gnuplot
*.options postamble1 = "using 2:3"

.options plotVT1Preamble="set term x11 font 'helvetica,13';
set title 'Ferroelectric capacitor Voltage';
set xlabel 'TIME (microseconds)'; set ylabel 'VOLTAGE (V)'"
.out plot element "capacitorferroelectric:cf1" 0 ut 1e6 scalex plotVT1Preamble in
"capacitorferroelectric_v.out"

.options plotVT1Preamble="set term x11 font 'helvetica,13';
set title 'Ferroelectric capacitor Current';
set xlabel 'TIME (microseconds)'; set ylabel 'Current (A)'"
.out plot element "capacitorferroelectric:cf1" 0 it 1e6 scalex plotVT1Preamble in
"capacitorferroelectric_i.out"

.options plotVT1Preamble="set term x11 font 'helvetica,13';
set title 'Input Voltage Source';
set xlabel 'TIME (microseconds)'; set ylabel 'Voltage (V)'"
.out plot term 1 vt 1e6 scalex plotVT1Preamble in "source_v.out"

.options plotVT1Preamble="set term x11 font 'helvetica,13';
set title 'Voltage across resistor';
set xlabel 'TIME (microseconds)'; set ylabel 'Voltage (V)'"
.out plot term 2 vt 1e6 scalex plotVT1Preamble in "res_v.out"

*pack in "capacitorferroelectric_combo.out"

```

```

*.out plot "capacitorferroelectric_combo.out" postamble
** .out plot element "capacitorferroelectric22:cf1" 0 xt in "capacitorferroelectric_x.out"
*.out plot element "capacitorferroelectric22:cf1" 0 ut stripx in
"capacitorferroelectric_v.out"
.end

```

Log File:

***** fREEDA 1.3 running on Sun Apr 20 22:54:49 2008 *****

*** Parsing input netlist ...

*** Expanding subcircuits ... done.

*** Initializing Elements ...cmax: 2.08002e-10
done.

*** Checking reference terminals ... done.

*** Starting analysis ...

```

-----
Matrix size = 3
Matrix nnz = 6
equed = 7.95719e-305
recip_pivot_growth = 1
1 / Condition number = 0.840131
info = 0
ferr = 9.70941e-308
berr = 1
No of nonzeros in factor L = 6
No of nonzeros in factor U = 6
No of nonzeros in L+U = 9
L\U MB 0.000      total MB needed 0.001      expansions 0
Using line search method.
Nonlinear analysis tolerance (ftol) = 6.12865e-06
Maximum number of nonlinear iterations per time-point (maxit) = 250
Using Lee and Lee's quasi-Newton updates.
--- Starting transient simulation ...

```

Number of nonlinear state variables: 1

Step	Time (s)	Residual	Recent Max	Max	

0	0.000000e+00	0.000000e+00	0.000000e+00	* 0.000000e+00	
1	5.000000e-07	6.274981e-13	6.274981e-13	6.274981e-13	

2	1.000000e-06	1.785239e-13	1.785239e-13	6.274981e-13
3	1.500000e-06	1.865175e-14	1.865175e-14	6.274981e-13
4	2.000000e-06	1.152591e-01	1.152591e-01	* 1.152591e-01
5	2.500000e-06	1.152591e-01	1.152591e-01	* 1.152591e-01
6	3.000000e-06	1.152591e-01	1.152591e-01	* 1.152591e-01
7	3.500000e-06	1.152591e-01	1.152591e-01	* 1.152591e-01
8	4.000000e-06	1.152591e-01	1.152591e-01	* 1.152591e-01
9	4.500000e-06	1.152591e-01	1.152591e-01	* 1.152591e-01
10	5.000000e-06	1.152591e-01	1.152591e-01	* 1.152591e-01

:	:	:	:	:	:
:	:	:	:	:	:

190	9.500000e-05	1.124087e-01	1.124087e-01	* 1.152591e-01
191	9.550000e-05	1.124087e-01	1.124087e-01	* 1.152591e-01
192	9.600000e-05	1.124087e-01	1.124087e-01	* 1.152591e-01
193	9.650000e-05	1.124087e-01	1.124087e-01	* 1.152591e-01
194	9.700000e-05	1.124087e-01	1.124087e-01	* 1.152591e-01
195	9.750000e-05	1.124087e-01	1.124087e-01	* 1.152591e-01
196	9.800000e-05	1.124087e-01	1.124087e-01	* 1.152591e-01
197	9.850000e-05	1.124087e-01	1.124087e-01	* 1.152591e-01
198	9.900000e-05	1.124087e-01	1.124087e-01	* 1.152591e-01
199	9.950000e-05	1.124087e-01	1.124087e-01	* 1.152591e-01
200	1.000000e-04	1.124087e-01	1.124087e-01	* 1.152591e-01

--- Maximum Residual: 0.115259

Plotting output file: capacitorferroelectric_v.out.

Plotting output file: capacitorferroelectric_i.out.

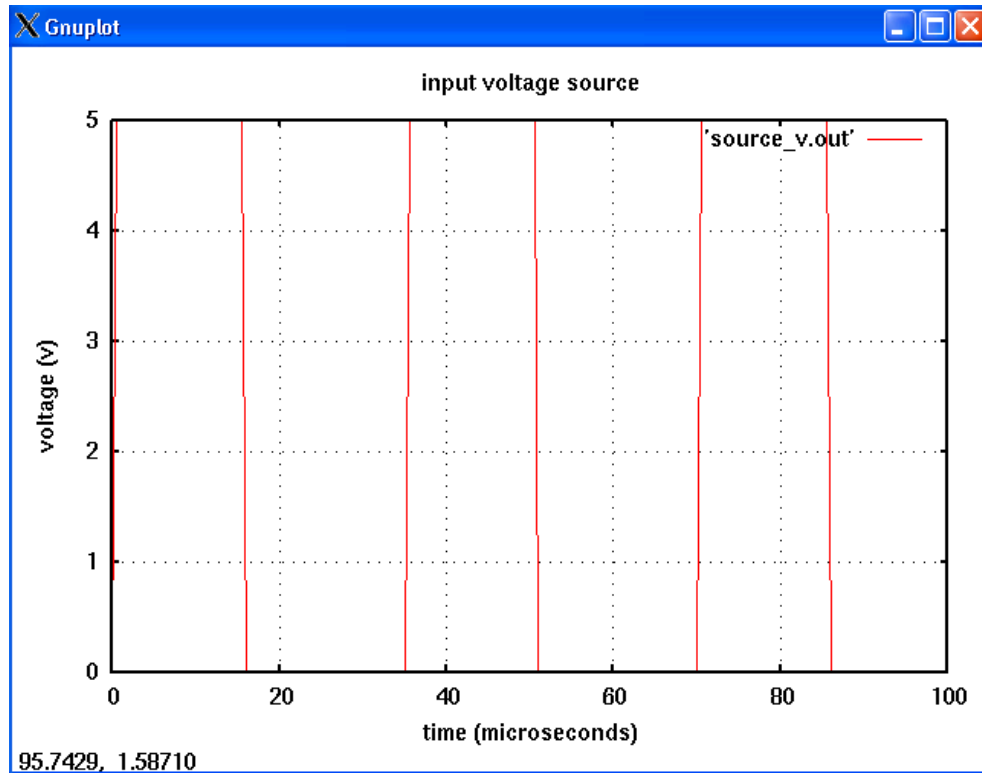
Plotting output file: source_v.out.

Plotting output file: res_v.out.

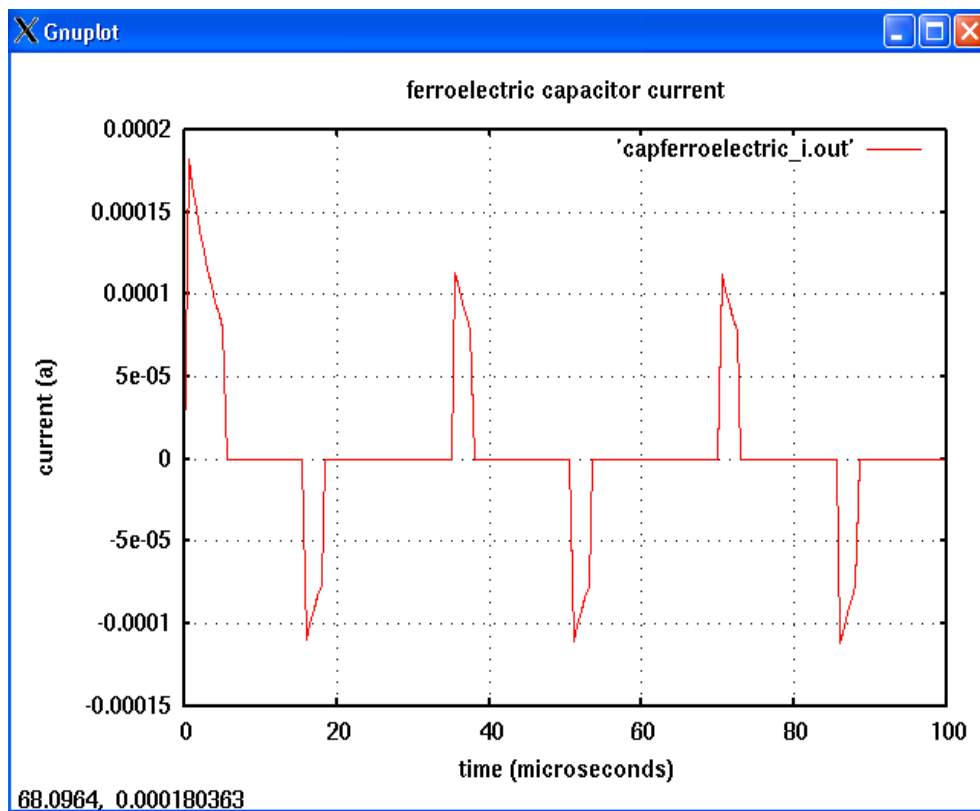
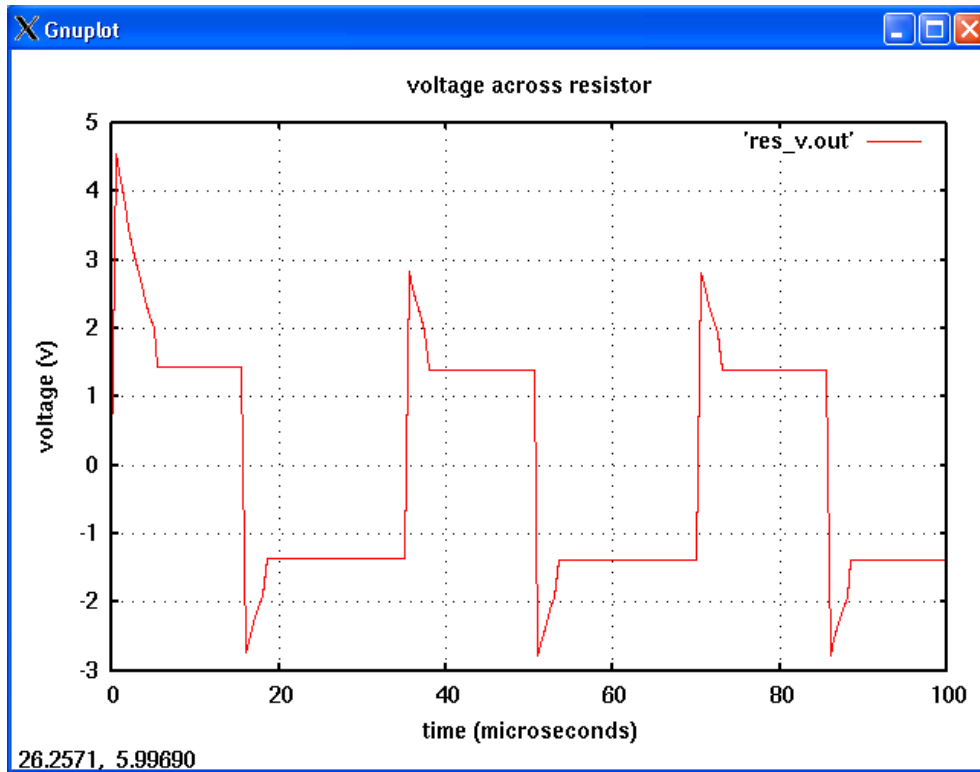
***** fREEDA 1.3 stopping on Sun Apr 20 22:54:52 2008 *****

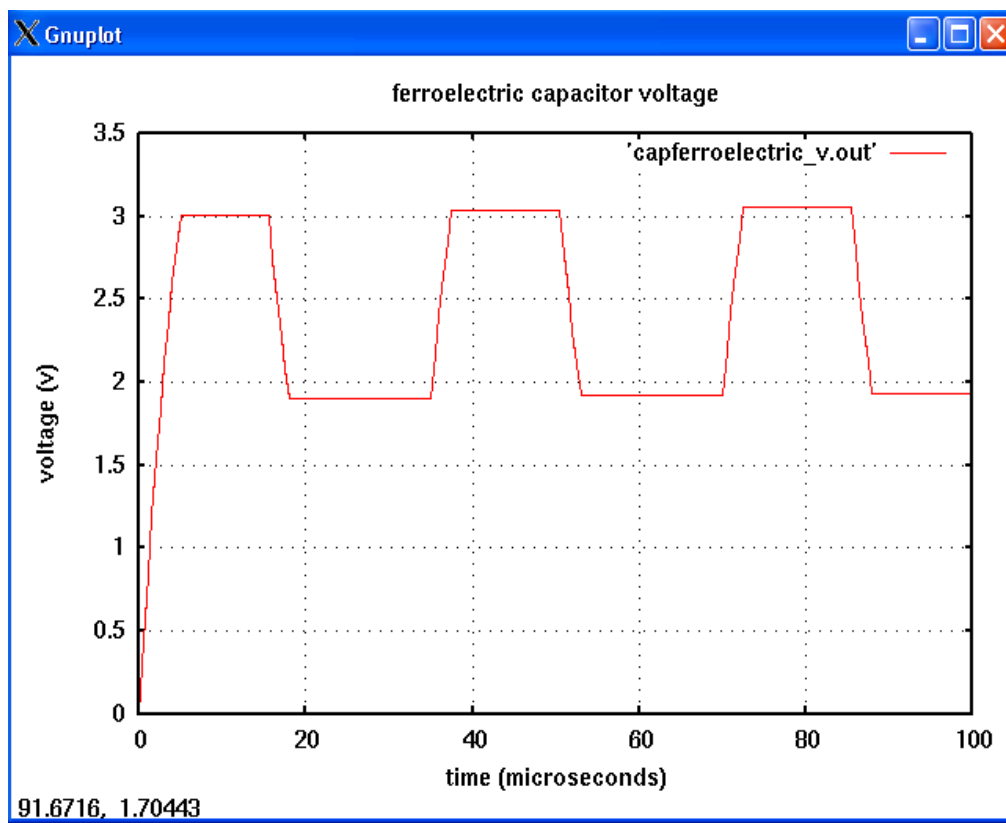
Simulation Results in fREEDA:

Input Voltage Pulse:

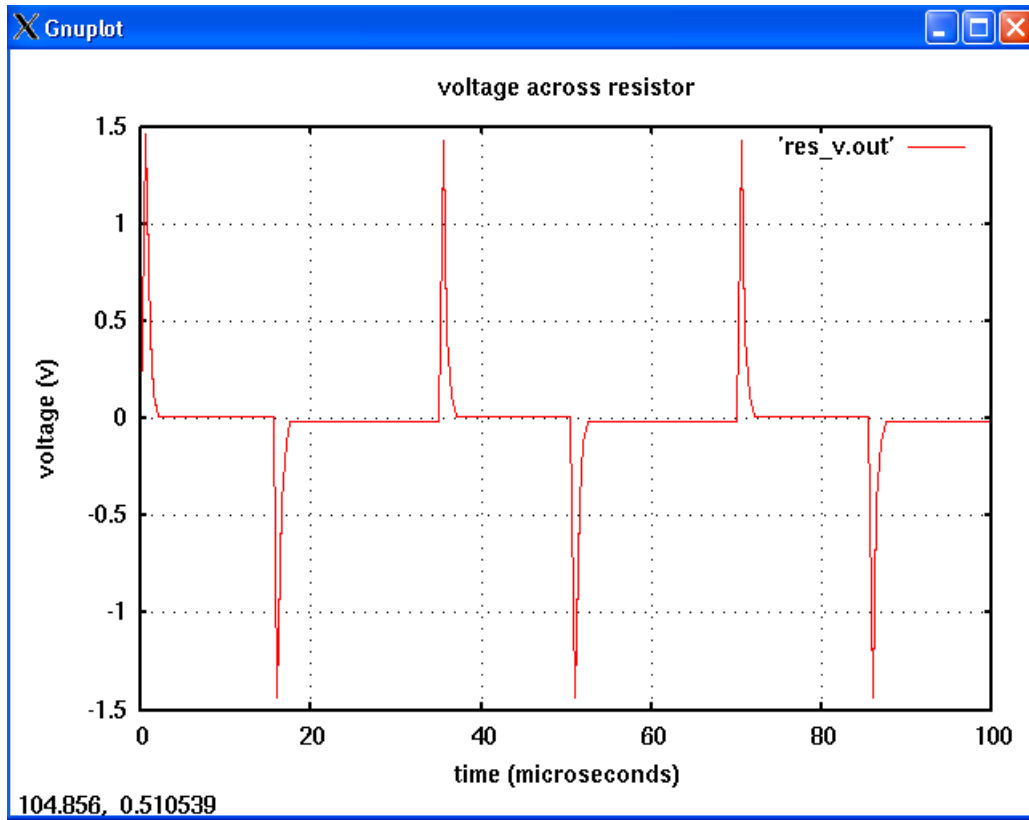


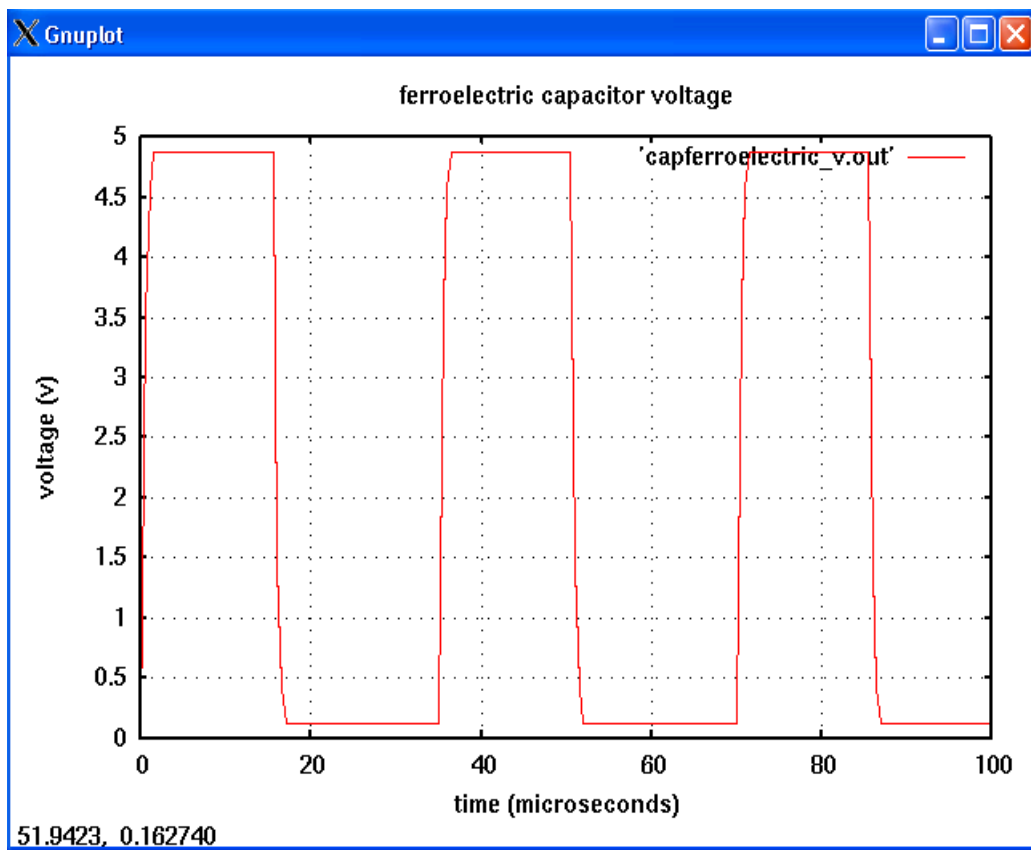
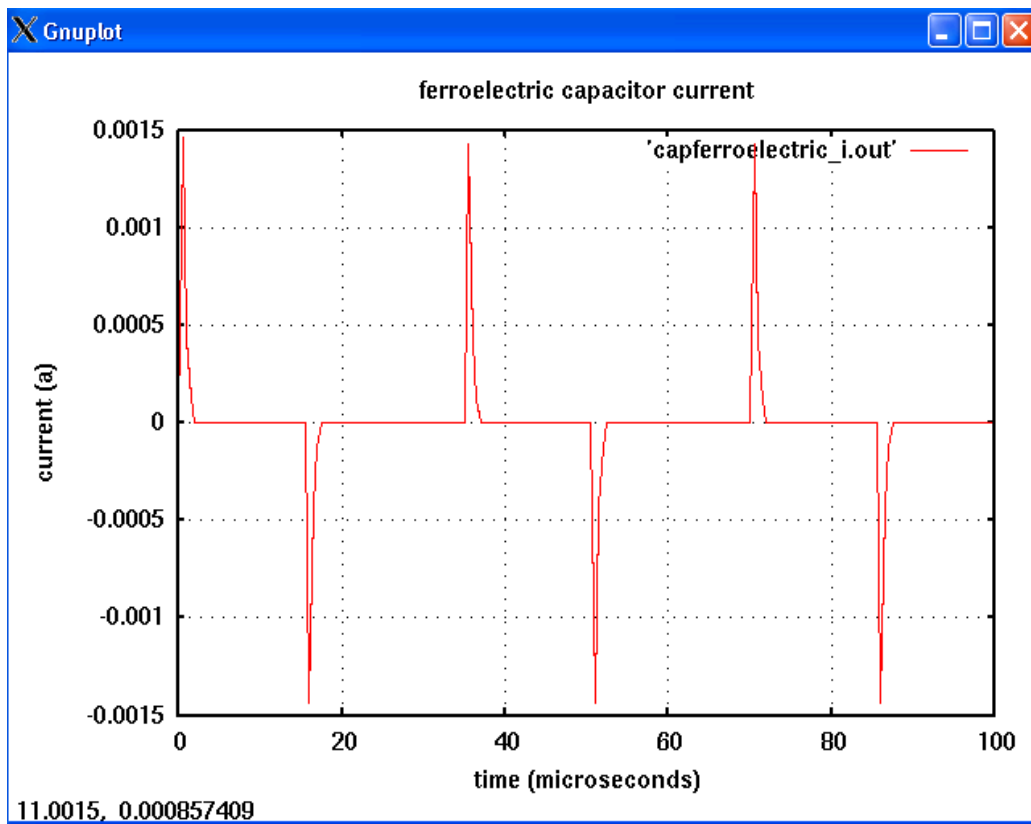
RC time constant $\sim T$:



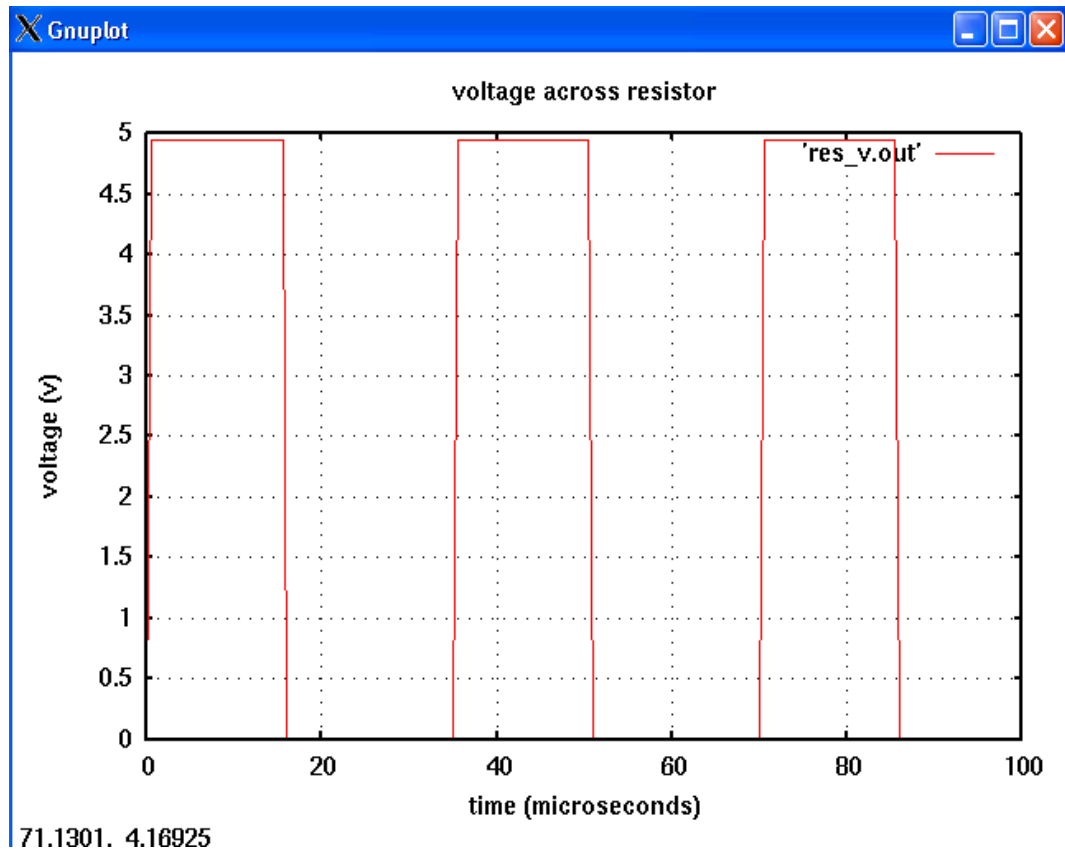


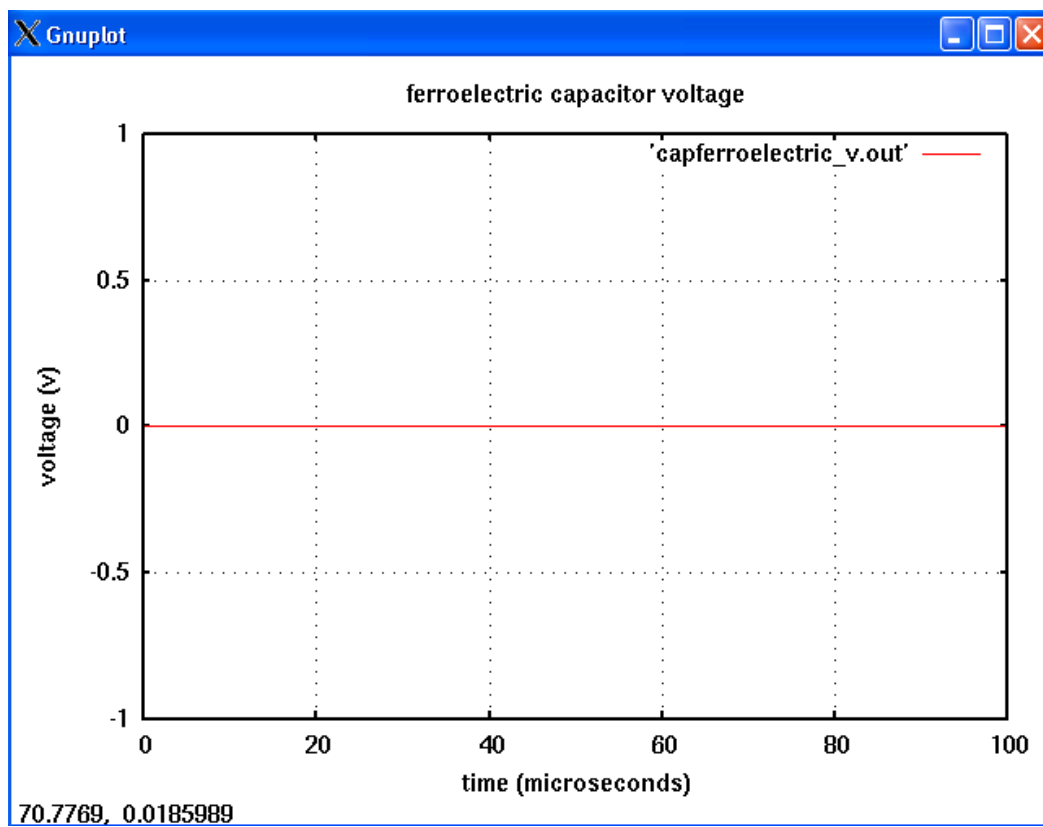
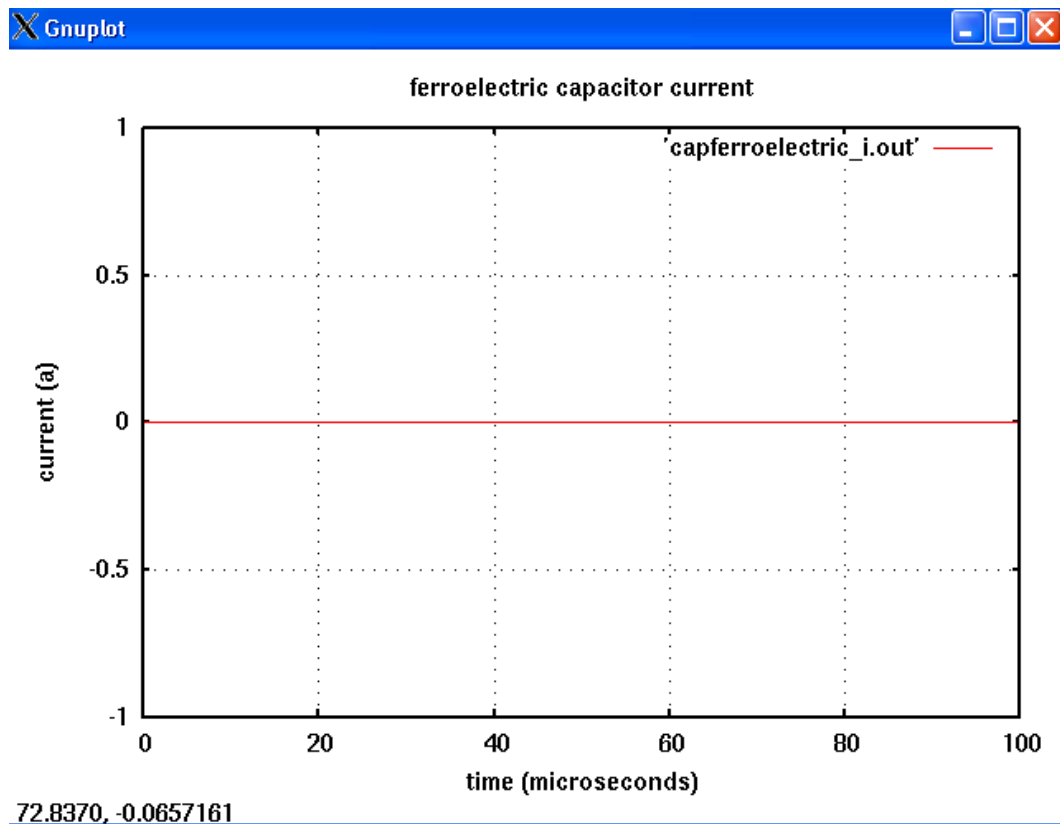
RC time constant $\ll T$:





RC time constant $\gg T$:






Version:

2008.04.20(2008 April 20)

Credits:

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References:

- [1] David R. Chase, Lee-Yin Chen, Robert York, "Modeling the Capacitive Nonlinearity in Thin-Film BST Varactors", IEEE MTT-S Vol 53 Oct, 2005.
 - [2] Michael B. Steer, W. Devereux Palmer, Robert York, "Multifunctional Adaptive Microwave Circuits and systems", Chap 4, 2008 Edition
 - [3] S.K. Streiffer, Cem Basceri, C.B. Parker, S.E.Lash, Angus I. Kingon, "Ferroelectricity in thin films: The dielectric response of fiber-textured $(\text{Ba}_x\text{Sr}_{1-x})\text{Ti}_{1+y}\text{O}$ thin films grown by chemical vapor deposition", J. Appl. Phys, Vol 86, N0.8, Oct 1999
 - [4] Cem Basceri, S.K. Streiffer, Angus I. Kingon, "The dielectric response as a function of temperature and film thickness of fiber-textured $(\text{Ba,Sr})\text{TiO}_3$ thin films grown by chemical vapor deposition, J. Appl. Phys Vol 82, Sept 1997
 - [5] J.D.Baniecki, T.Shioga, K. Kurihara, N.Kamehara, "A study of current transport in thin-film capacitors containing a voltage-dependent interface state charge distribution.", J. Appl Phys, Vol 97, May 2005
 - [6] <http://www.kpsec.freeuk.com/capacit.htm>
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